

## Corrigendum

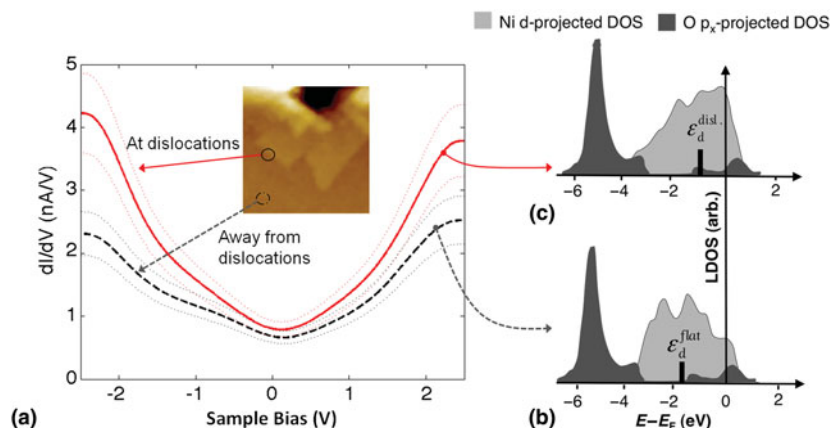
# Plasticity-induced oxidation reactivity on Ni(100) studied by scanning tunneling spectroscopy – CORRIGENDUM

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doi: 10.1557/mrc.2011.17, Published by Cambridge University Press, 14 October 2011.

Figure 2 as published is missing an axis label.

The corrected Figure 2 appears below.



**Figure 2.** (a) In situ electronic structure characterization of the Ni(100) surface upon STM tip-induced plasticity. Differential tunneling conductance measurements,  $dI/dV$ , obtained both at dislocation steps (solid curve) and away from dislocations (dashed curve). Each curve is the average of over 100 point spectra from three different indentations. The error in  $dI/dV$  measured by standard deviation is  $\pm 18\%$ , represented by dashed enveloping curves. Schematic density of state diagrams illustrate how an increase in DOS around  $E_F$  can be interpreted as an up-shift in the Ni d-band center from (b)  $\epsilon_d^{\text{flat}}$  at the undamaged surface to (c)  $\epsilon_d^{\text{disl}}$  at dislocations (after [14]).

## Reference

F.W. Herbert, K.J. Van Vliet, and B. Yildiz: Plasticity-induced oxidation reactivity on Ni(100) studied by scanning tunneling spectroscopy. *MRS Communications*, doi: 10.1557/mrc.2011.17, Published online 14 October 2011.